

**SANYO**

No.4318

**2SJ308**

P-Channel MOS Silicon FET

Very High-Speed  
Switching Applications**Features**

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating mounting.

勝特力材料 886-3-5753170

勝特力电子(上海) 86-21-54151736

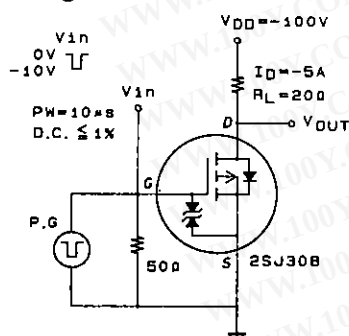
勝特力电子(深圳) 86-755-83298787

[Http://www.100y.com.tw](http://www.100y.com.tw)**Absolute Maximum Ratings at Ta = 25°C**

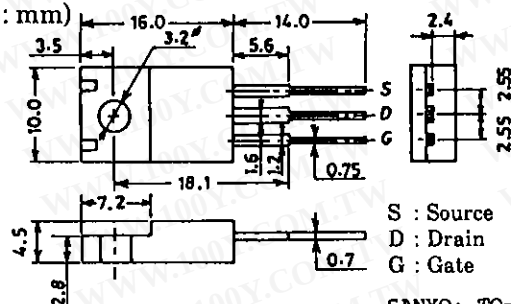
|                             |           |                                                | unit  |
|-----------------------------|-----------|------------------------------------------------|-------|
| Drain to Source Voltage     | $V_{DS}$  | -250                                           | V     |
| Gate to Source Voltage      | $V_{GS}$  | ±30                                            | V     |
| Drain Current(DC)           | $I_D$     | -9                                             | A     |
| Drain Current(Pulse)        | $I_{DP}$  | $PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$ | -36 A |
| Allowable Power Dissipation | $P_D$     | 2.0                                            | W     |
|                             |           | $T_c = 25^\circ C$                             | 40 W  |
| Channel Temperature         | $T_{ch}$  | 150                                            | °C    |
| Storage Temperature         | $T_{stg}$ | -55 to +150                                    | °C    |

**Electrical Characteristics at Ta = 25°C**

|                                            |               |                                  | min  | typ  | max  | unit     |
|--------------------------------------------|---------------|----------------------------------|------|------|------|----------|
| D-S Breakdown Voltage                      | $V_{(BR)DS}$  | $I_D = -1mA, V_{GS} = 0$         | -250 |      |      | V        |
| G-S Breakdown Voltage                      | $V_{(BR)GS}$  | $I_G = \pm 100\mu A, V_{DS} = 0$ | ±30  |      |      | V        |
| Zero Gate Voltage Drain Current            | $I_{DSS}$     | $V_{DS} = -250V, V_{GS} = 0$     |      |      | -100 | $\mu A$  |
| Gate to Source Leakage Current             | $I_{GSS}$     | $V_{GS} = \pm 25V, V_{DS} = 0$   |      |      | ±10  | $\mu A$  |
| Cutoff Voltage                             | $V_{GS(off)}$ | $V_{DS} = -10V, I_D = -1mA$      | -1.5 |      | -2.5 | V        |
| Forward Transfer Admittance                | $ Y_{fs} $    | $V_{DS} = -10V, I_D = -5A$       | 6    | 10   |      | S        |
| Static Drain to Source on State Resistance | $R_{DS(on)}$  | $I_D = -5A, V_{GS} = -10V$       | 0.35 | 0.48 |      | $\Omega$ |
| Input Capacitance                          | $C_{iss}$     | $V_{DS} = -20V, f = 1MHz$        |      | 2700 |      | pF       |
| Output Capacitance                         | $C_{oss}$     | $V_{DS} = -20V, f = 1MHz$        |      | 500  |      | pF       |
| Reverse Transfer Capacitance               | $C_{rss}$     | $V_{DS} = -20V, f = 1MHz$        |      | 225  |      | pF       |
| Turn-ON Delay Time                         | $t_{d(on)}$   | See specified Test Circuit.      |      | 40   |      | ns       |
| Rise Time                                  | $t_r$         | "                                |      | 75   |      | ns       |
| Turn-OFF Delay Time                        | $t_{d(off)}$  | "                                |      | 320  |      | ns       |
| Fall Time                                  | $t_f$         | "                                |      | 260  |      | ns       |
| Diode Forward Voltage                      | $V_{SD}$      | $I_S = -9A, V_{GS} = 0$          | -1.0 | -1.5 |      | V        |

**Switching Time Test Circuit****Package Dimensions 2063**

(unit: mm)

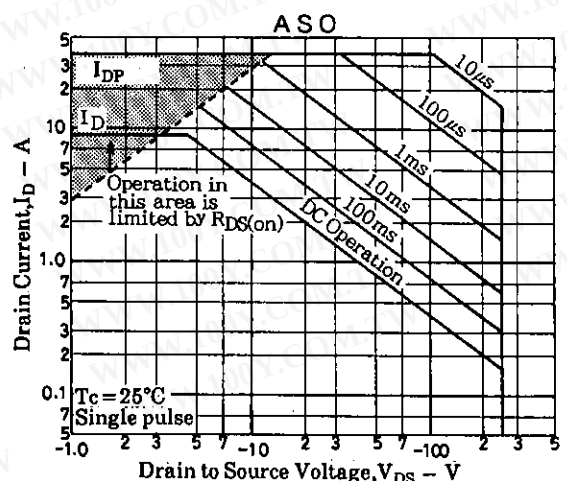
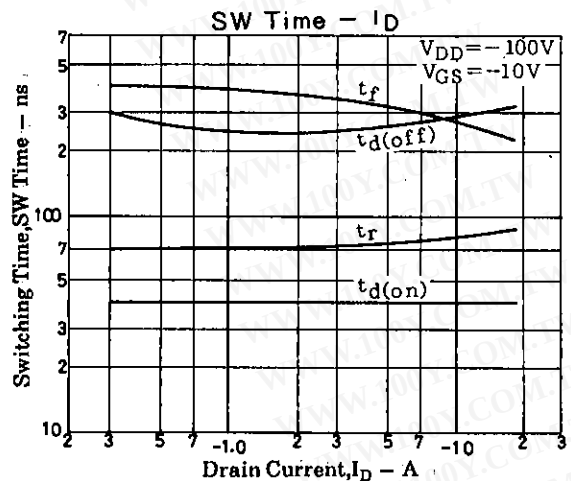
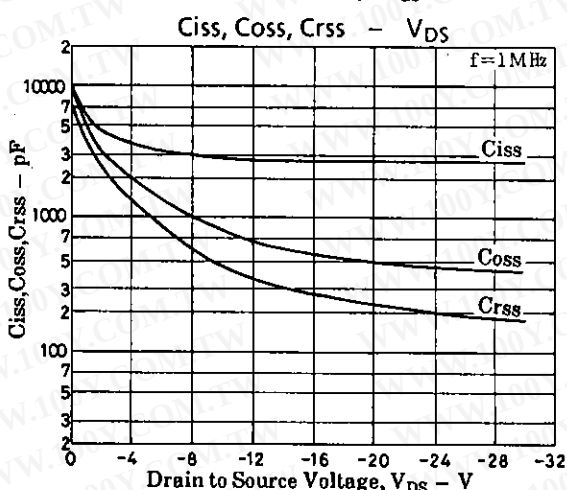
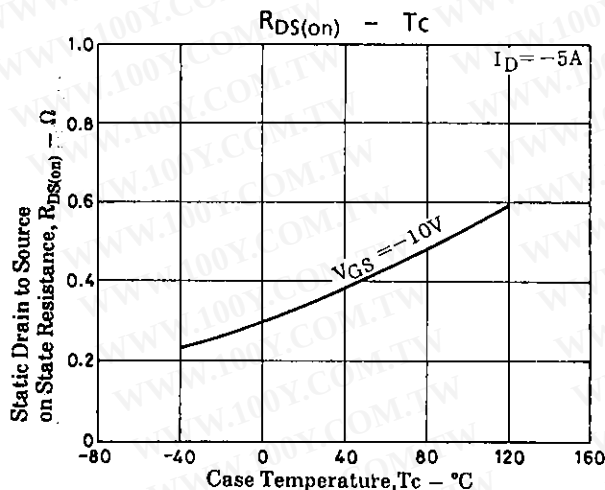
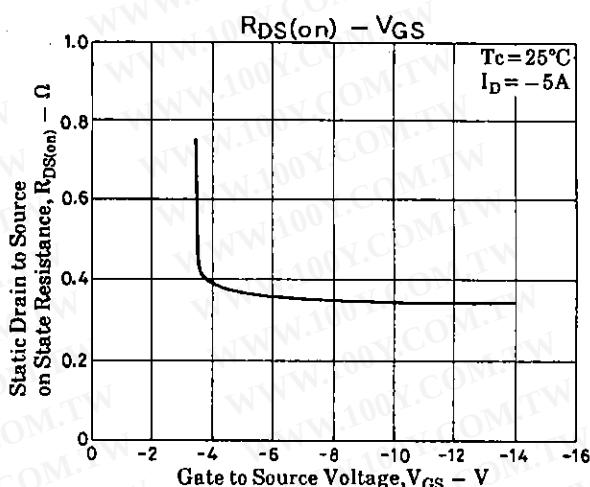
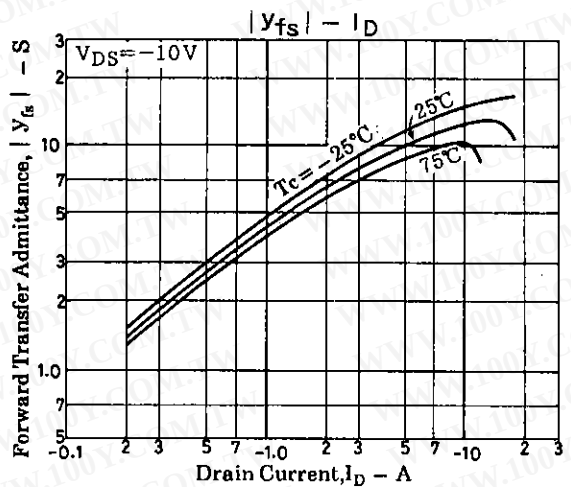
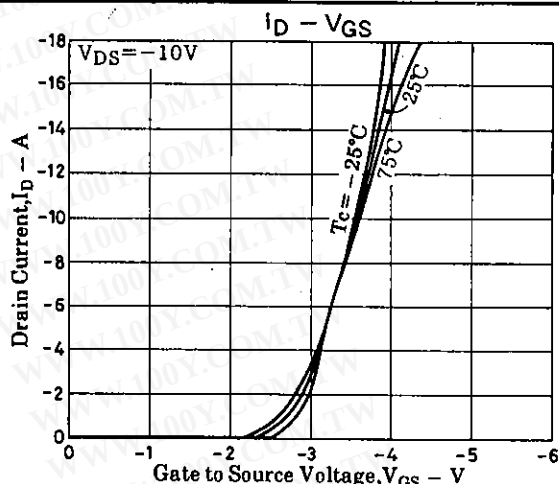
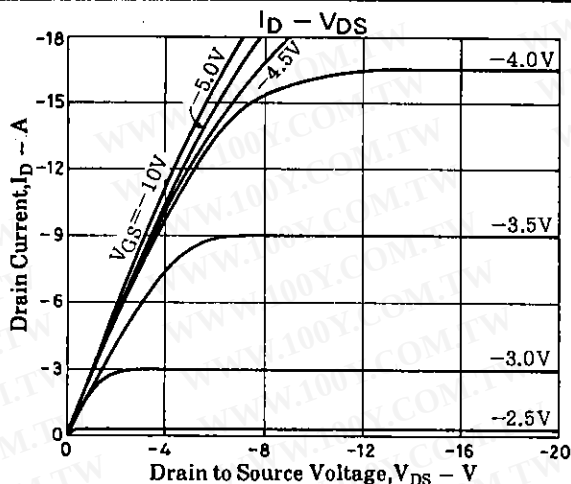


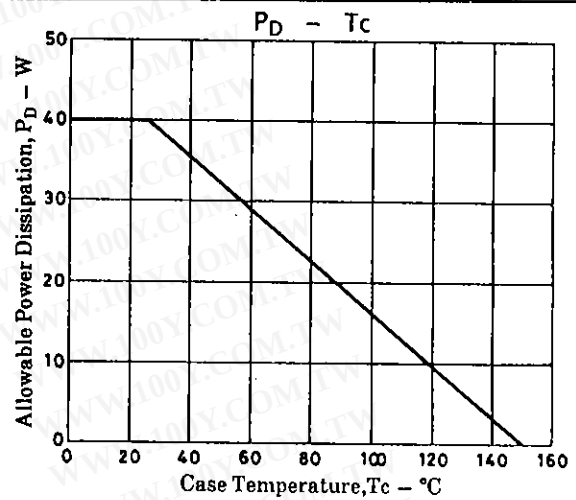
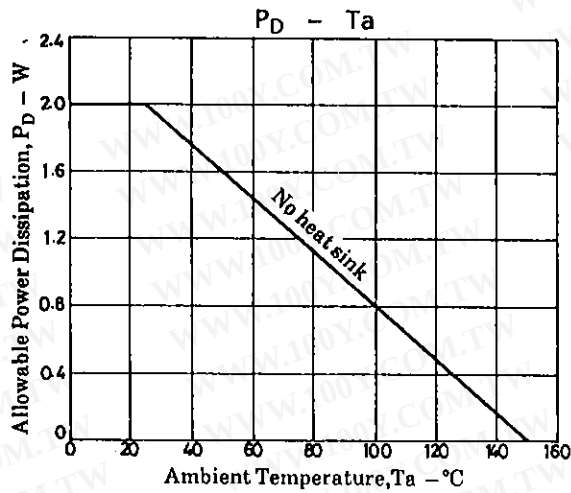
SANYO: TO-220ML

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